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**BSS123** 

#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
100V	6.0Ω @ V <sub>GS</sub> = 10V	0.17A

### **Description and Applications**

These N-Channel enhancement mode field effect transistors are produced using DIODES proprietary, high density, uses advanced trench technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. These products are particularly suited for low voltage, low current applications such as:

- Small Servo Motor Control
- Power MOSFET Gate Drivers
- Switching Applications

### **Features and Benefits**

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- High Drain-Source Voltage Rating
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

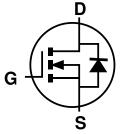
### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

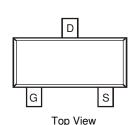




Top View



**Equivalent Circuit** 



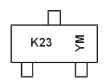
## **Ordering Information (Note 5)**

Part Number	Qualification	Case	Packaging
BSS123-7-F	Commercial	SOT23	3,000 / Tape & Reel
BSS123Q-13	Automotive	SOT23	10,000 / Tape & Reel
BSS123Q-7	Automotive	SOT23	3,000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



K23 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	Т	U	V	W	Χ	Υ	Z	Α	В	С	D	Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	-1	2	2	1	5	6	7	ο	٥	$\cap$	N	D



## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	100	V
Gate-Source Voltage	Continuous	$V_{GSS}$	±20	V
Continuous Dunin Courset (Note C) // 10//	Continuous	I <sub>D</sub>	170	mA
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Pulsed	I <sub>DM</sub>	680	IIIA

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	300	mW
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6)	$R_{\theta JA}$	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

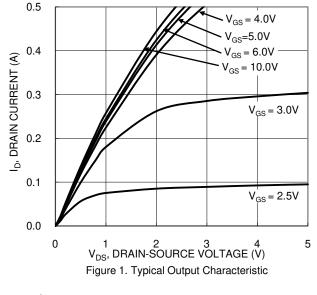
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)		•				•
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$
		-	-	0.1	μА	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	30	μΑ	$V_{DS} = 100V, V_{GS} = 0V$ @ $T_A = 150^{\circ}C$ (Note 8)
		-	-	10	nA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage, Forward	I <sub>GSSF</sub>	-	-	50	nA	$V_{GS} = 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.8	1.4	2.0	V	$V_{DS} = V_{GS}$ , $I_D = 1mA$
Static Drain-Source On-Resistance		-	-	6.0	Ω	$V_{GS} = 10V, I_D = 0.17A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	-	10		$V_{GS} = 4.5V, I_D = 0.17A$
Forward Transfer Admittance	<b>g</b> FS	80	370	-	ms	$V_{DS} = 10V$ , $I_D = 0.17A$ , $f = 1.0KHz$
Diode Forward Voltage	V <sub>SD</sub>	-	0.84	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 0.34A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	-	22	60		
Output Capacitance	Coss	-	3.5	15	pF	$V_{DS} = 25V$ , $V_{GS} = 0V$ , $f = 1.0MHz$
Reverse Transfer Capacitance	C <sub>rss</sub>	-	2.0	6		
SWITCHING CHARACTERISTICS (Note 8)						
Turn-On Delay Time	t <sub>D(ON)</sub>	-	-	8	ns	
Turn-On Rise Time	t <sub>R</sub>	-	-	8	ns	$V_{GS} = 10V, V_{DD} = 30V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	-	13	ns	$I_D = 0.28A, R_{GEN} = 50\Omega$
Turn-Off Fall Time	t <sub>F</sub>	-	-	16	ns	

Notes:

- 6. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at http://www.diodes.com/package-outlines.html.
- 7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to production testing.





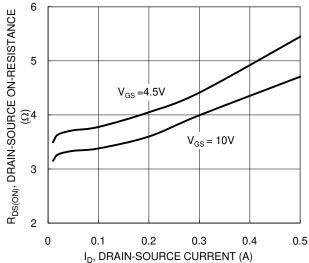


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

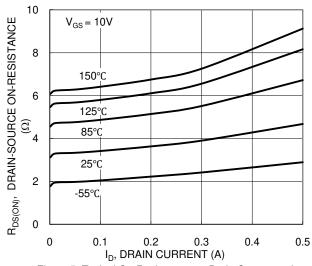
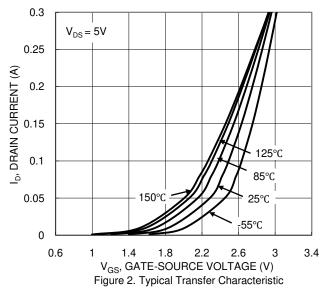


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



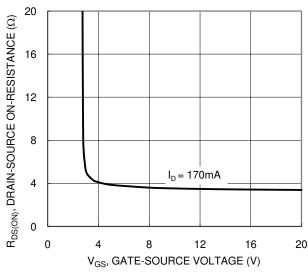
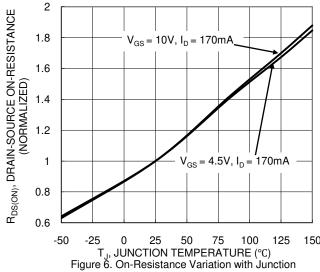
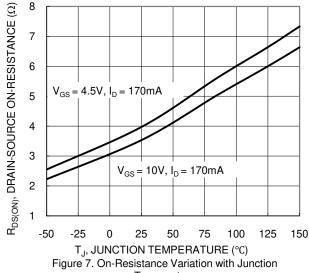


Figure 4. Typical Transfer Characteristic

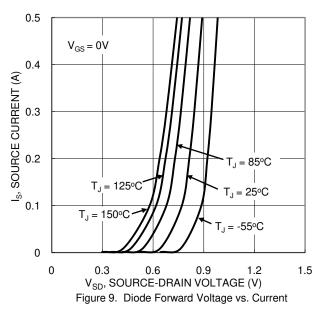


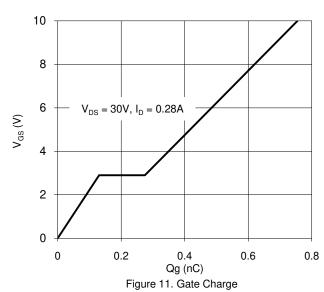
Temperature





Temperature





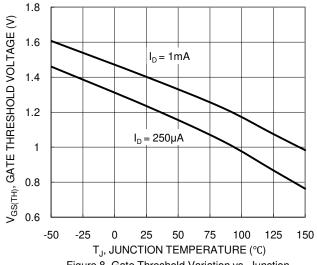
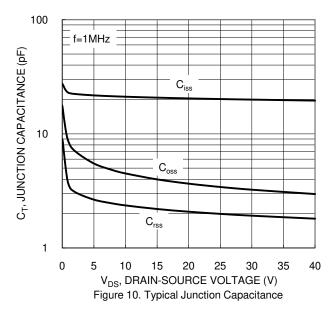
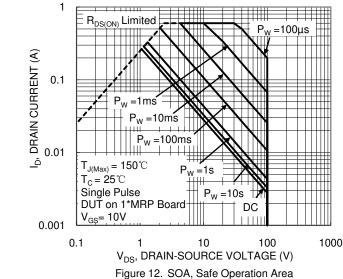


Figure 8. Gate Threshold Variation vs. Junction Temperature







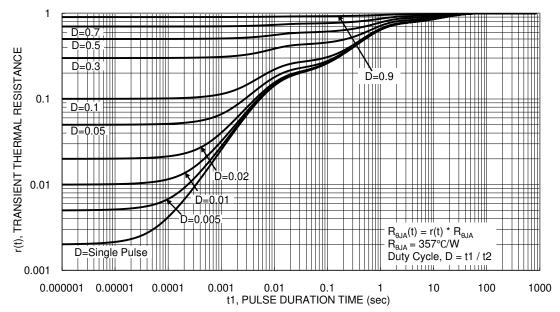


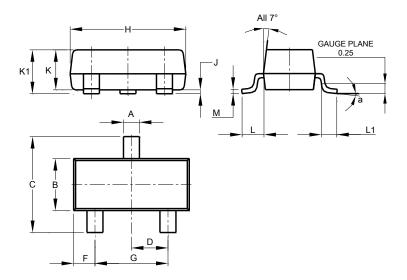
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

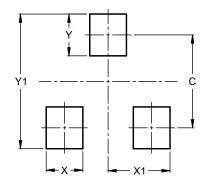
### SOT23



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



#### SOT23

Dimensions	Value (in mm)
O	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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